

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Patent Application of	)	
	)	
Tsukasa OOISHI	)	Group Art Unit: Unassigned
	)	
Application No.: Unassigned	)	Examiner: Unassigned
	)	
Filed: October 29, 2003	)	Confirmation No.: Unassigned
	)	
For: SEMICONDUCTOR DEVICE AND	)	
SEMICONDUCTOR MEMORY DEVICE	)	
PROVIDED WITH INTERNAL	)	
CURRENT SETTING ADJUSTMENT	)	
CIRCUIT	)	

**FIRST  
INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Date: October 29, 2003

Sir:

In accordance with the duty of disclosure as set forth in 37 C.F.R. § 1.56, Applicant hereby submits the following information in conformance with 37 C.F.R. §§ 1.97 and 1.98.

Pursuant to 37 C.F.R. § 1.98, a copy of each of the documents cited is enclosed.

However, copies of the listed U.S. patents and U.S. patent application publications are not enclosed since it is no longer required according to the July 11, 2003 waiver of the requirement for copies of cited U.S. patents and U.S. patent application publications in national patent applications filed after June 30, 2003 and international applications entering the national stage under 35 U.S.C. § 371 after June 30, 2003.

1. USP 6,347,056
2. USP 6,201,754
3. USP 6,337,828
4. USP 6,256,224
5. JP 11-339470
6. "A 10ns Read and Write Non-Volatile Memory Array Using a Magnetic Tunnel Junction and FET Switch in Each Cell", IEEE ISSCC Digest of Technical Papers
7. "Forefront of Non-Volatile Memory the Future in Intel's Mind: From Flash Memory to OUM", Nikkei Microdevices

8. U.S. Publication No. 2003/0081453

Reference Nos. 5 - 7 are cited on pages 1 and 2 of the specification.

The documents are being submitted within three (3) months of the filing or entry of the national stage of this application or before the first Office Action on the merits, whichever is later. Since documents are being filed within the time period set forth in 37 C.F.R. § 1.97(b) no fee or statement is required.

To assist the Examiner, the documents are listed on the attached form PTO-1449. It is respectfully requested that an Examiner-initialed copy of this form be returned to the undersigned.

Respectfully submitted,

BURNS, DOANE, SWECKER & MATHIS, L.L.P.

Date: October 29, 2003

By:

  
Ellen Marcie Emas  
Registration No. 32,131

P.O. Box 1404  
Alexandria, Virginia 22313-1404  
(703) 836-6620

Substitute for forms 1449A/PTO & 1449B/PTO	ATTORNEY'S DKT No.	APPLICATION No.
	009683-485	Unassigned
	APPLICANT	
	Tsukasa OOISHI	
<b>FIRST INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>	FILING DATE	GROUP
	October 28, 2003	Unassigned

U.S. PATENT DOCUMENTS				
Examiner Initials	Document Number	Kind Code (if known)	Name of Patentee or Applicant of Cited Document	Issue/Publication Date (MM-DD-YYYY)
	6,347,056		Ledford et al.	02-12-2002
	6,201,754		Ooishi et al.	03-13-2001
	6,337,828		Ooish et al.	01-08-2002
	6,256,224		Perner et al.	07-03-2001
	2003/0081453		Hidaka	05-01-2003

FOREIGN PATENT DOCUMENTS					
Examiner Initials	Document Number	Kind Code (if known)	Country	Date of Publication (MM-DD-YYYY)	Translation Yes No
	11-339470		Japan	12-10-1999	X

NON PATENT LITERATURE DOCUMENTS	
Examiner Initials	Include name of author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
	Roy SCHEUERLEIN et al., "A 10ns Read and Write Non-Volatile Memory Array using a Magnetic Tunnel Junction and FET Switch in Each Cell," IEEE ISSCC Digest of Technical Papers, February 2000, pp. 94-95, 128-129, 409-410.
	NIKKEI MICRODEVICES, "Forefront of Non-Volatile Memory The Future in Intel's Mind: From Flash Memory to "OUM", " March 2002, pp. 65-78 (with partial English Translation).

Examiner Signature		Date Considered	
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with M.P.E.P. § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. SEND TO: Assistant Commissioner for Patents, Washington, DC 20231.